L Number	Hits	S arch Text	DB	Tim stamp
	2	(singl adj crystal).clm. and (amoprhiz r	USPAT;	2003/09/15
		am rphizing or amorphiz d or	US-PGPUB;	14:49
		amorphizati n).clm. and laser.clm.	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4526	yamamoto and fujitsu	USPAT;	2003/09/15
			US-PGPUB;	11:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	1	(yamamoto and fujitsu) and (shallow and	USPAT;	2003/09/15
	-	deep).clm.	US-PGPUB;	11:46
		usep).cimi.	EPO; JPO;	11.40
			DERWENT;	
			IBM TDB	
	•		_	2002/00/45
•	2	yamamoto and tomonari and fujitsu	USPAT;	2003/09/15
			US-PGPUB;	11:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5353	parasitic adj resistance	USPAT;	2003/09/15
			US-PGPUB;	11:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	83	(parasitic adj resistance) and (single adj	USPAT;	2003/09/15
		crystal).clm.	US-PGPUB;	11:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
- 1	4	((parasitic adj resistance) and (single adj	USPAT;	2003/09/15
		crystal).clm.) and laser.clm.	US-PGPUB;	11:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2	(parasitic adj resistance).ti,ab,clm. and	USPAT;	2003/09/15
	_	(single adj crystal).ti,ab,clm. and	US-PGPUB;	11:52
		laser.ti,ab,clm. and ion.ti,ab,clm. and	EPO; JPO;	
		(implant or implanting or implanted or	DERWENT;	
		implantation).ti,ab,clm.	IBM_TDB	
_	1	((parasitic adj resistance).ti,ab,clm. and	USPAT;	2003/09/15
-	•		1	
		(single adj crystal).ti,ab,clm. and	US-PGPUB;	11:52
		laser.ti,ab,clm. and ion.ti,ab,clm. and	EPO; JPO;	
ļ		(implant or implanting or implanted or	DERWENT;	
	İ	implantation).ti,ab,clm.) and	IBM_TDB	
		(amorphous).ti,ab,clm.		

	0	((parasitic adj r sistance).ti,ab,clm. and	USPAT;	2003/09/15
		(single adj rystal).ti,ab,clm. and	US-PGPUB;	11:52
		laser.ti,ab, lm. and i n.ti,ab, lm. and	EPO; JPO;	
		(implant rimplanting rimplanted or	DERWENT;	
	İ	implantati n).ti,ab,clm.) and	IBM_TDB	
		(obliquie).ti,ab,clm.		
-	1	((parasitic adj resistance).ti,ab,clm. and	USPAT;	2003/09/15
		(single adj crystal).ti,ab,clm. and	US-PGPUB;	11:52
ı		laser.ti,ab,clm. and ion.ti,ab,clm. and	EPO; JPO;	
		(implant or implanting or implanted or	DERWENT;	
		implantation).ti,ab,clm.) and	IBM_TDB	
		(oblíque).ti,ab,clm.		_
-	2	(parasitic adj resistance) and (single adj	USPAT;	2003/09/15
		crystal) and laser and ion and (implant or	US-PGPUB;	11:53
		implanting or implanted or implantation)	EPO; JPO;	
		and oblique and (amorphous or amorphize	DERWENT;	
		or amoprhized or amorphizing or	IBM_TDB	
	38	amorphization)	HEDAT	2003/00/45
-	36	(single adj crystal) and (oblique near5 laser)	USPAT; US-PGPUB;	2003/09/15 11:56
			1	11:50
			EPO; JPO; DERWENT;	
			IBM TDB	
_	0	((single adj crystal) and (oblique near5	USPAT;	2003/09/15
_		laser)) and (parasitic near resistance)	US-PGPUB;	11:56
		rassi,, and (parasitio nour resistance)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	633	(single adj crystal) and (oblique and laser)	USPAT;	2003/09/15
			US-PGPUB;	11:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	((single adj crystal) and (oblique and laser))	USPAT;	2003/09/15
		and (parasitic near resistance)	US-PGPUB;	11:57
			EPO; JPO;	
	}		DERWENT;	
			IBM_TDB	
-	13	((single adj crystal) same laser same	USPAT;	2003/09/15
		(oblique or slanted or slanting or	US-PGPUB;	12:51
		diagonal)).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/00/45
•	1	((single adj crystal) same laser same	USPAT;	2003/09/15
		(oblique or slanted or slanting or diagonal) same (ion) same (implant or implanted or	US-PGPUB; EPO; JPO;	12:51
		implanting or implantation)).ti,ab,clm.	DERWENT:	
		p.ag or implantation/j.tijabjeiiii.	IBM_TDB	
	1	((singl adj crystal) same las r same	USPAT;	2003/09/15
	1	(blique or slant d r slanting r diagonal)	US-PGPUB;	12:51
		sam (i n) same (implant r implanted or	EPO; JPO;	
	1	implanting r implantation))	DERWENT;	
		· · · · · · · · · · · · · · · · · · ·	IBM_TDB	

•	439	((ingle adj crystal) and las rand (blique r lanted rslanting or diag nal) and (i n) and (implant or implanted or implanting r implantati n))	USPAT; US-P PUB; EPO; JPO; DERWENT;	2003/09/15 12:52
-	8	(((single adj crystal) and laser and (oblique or slanted or slanting or diagonal) and (ion) and (implant or implanted or implanting or	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/09/15 12:52
		implantation))) and ((amporphize or amorphizing or amorphized or amorphous) same oblique)	DERWENT; IBM_TDB	
-	6	(parasitic near resistance) and (laser near (anneal or annealing or annealed or irradiation or irradiate or irradiating or irradiated)) and (ion near (implant or implanting or implantation)) and oblique	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:50
-	3	(parasitic near resistance) and (laser near (anneal or annealing or annealed or irradiation or irradiate or irradiating or irradiated)) and (ion near (implant or implanting or implanted or implantation)) and (oblique or slant or slanted or diagonal) and (amorphous or amorphize or amorphizing or amorphized) and (single adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:52
-	21	crystal) (parasitic near resistance) and (laser near (anneal or annealing or annealed or irradiation or irradiate or irradiating or irradiated)) and (ion near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:53
-	712	((ion near (implant or implanting or implanted or implantation)) near5 oblique)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:53
-	24	((ion near (implant or implanting or implanted or implantation)) near5 oblique) same (amorphous or amorphize or amorphizing or amorphized)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:54
-	2	((ion near (implant or implanting or implanted or implantation)) near5 oblique) same (amorphous or amorphize or amorphizing or amorphized) same (single adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/15 14:54

•	2	(((i n near (implant r implanting or	USPAT;	2003/09/15
		implanted rimplantati n)) near5 bliqu)	US-PGPUB;	14:55
		sam (am rph us ram rphize or	EPO; JPO;	
		am rphizing ram rphized)) and (single adj	DERWENT;	
		crystal)	IBM_TDB	
-	31	(((ion near (implant or implanting or	USPAT;	2003/09/15
		implanted or implantation)) near5 oblique)	US-PGPUB;	14:55
		and (amorphous or amorphize or	EPO; JPO;	
		amorphizing or amorphized)) and (single adj	DERWENT;	
	İ	crystal)	IBM_TDB	
-	11	(((ion near (implant or implanting or	USPAT;	2003/09/15
		implanted or implantation)) near5 oblique)	US-PGPUB;	14:56
		and (amorphous or amorphize or	EPO; JPO;	
		amorphizing or amorphized)) and (single adj	DERWENT;	
		crystal) and laser	IBM_TDB	
-	1	((amorphize or amorphized or amorphous or	USPAT;	2003/09/15
		amorphizing) near5 oblique near5 (ion or	US-PGPUB;	14:57
	:	atom)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	((amorphize or amorphized or amorphous or	USPAT;	2003/09/15
		amorphizing) near10 oblique near10 (ion or	US-PGPUB;	14:57
		atom)).clm.	EPO; JPO;	
			DERWENT;	•
			IBM_TDB	
-	14	((amorphize or amorphized or amorphous or	USPAT;	2003/09/15
		amorphizing) near10 oblique near10 (ion or	US-PGPUB;	14:58
		atom))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	625	(oblique near5 (ion or atom) near5 (implant	USPAT;	2003/09/15
	i	or implantation or implantated or	US-PGPUB;	14:59
		implantating))	EPO; JPO;	
			DERWENT;	
	92	(abligue near (ion or story) was of (ion)	IBM_TDB	2002/00/45
-	82	(oblique near5 (ion or atom) near5 (implant	USPAT;	2003/09/15
		or implantation or implantated or	US-PGPUB;	14:59
		implantating)).clm.	EPO; JPO;	
			DERWENT;	
	o	(ablique pears (ien er etem) (imm)	IBM_TDB	2002/00/45
-	"	(oblique near5 (ion or atom) near5 (implant or implantation or implantated or	USPAT;	2003/09/15 14:59
		or implantation or implantated or implantating)).clm. and laser.clm.	US-PGPUB;	14:03
		p.antating//.ciiii. anu laser.ciiii.	EPO; JPO; DERWENT;	
			IBM_TDB	
_	7	(oblique near5 (ion or atom) near5 (implant	USPAT;	2003/09/15
	•	or implantation or implantated or	US-PGPUB;	15:00
			1	13.00
		implantating)).clm_and lecor	EDO: IDO:	
		implantating)).clm. and laser	EPO; JPO; DERWENT;	

<u> </u>	0	/ bligger ark (i m yet m) near (include	HEDAT.	2003/09/15
•	U	(blique n ar5 (i n rat m) near5 (implant rimplantati n rimplantat d r	USPAT; US-PGPUB;	2003/09/15 15:00
	1	implantating)).clm. and laser and (parasitic	EPO; JPO;	13:00
		n ar resistan e)	DERWENT;	
		n arresistan e;	IBM_TDB	
_	14	(oblique near5 (ion or atom) near5 (implant	i —	2003/09/15
_	1-0	or implantation or implantated or	USPAT;	15:00
	Ì	implantation or implantated or implantating)).clm. and (single adj crystal)	US-PGPUB;	15:00
		implantating)).cim. and (single adj crystal)	EPO; JPO; DERWENT;	
			IBM_TDB	
_	9	(oblique near10 (ion or atom) near10	USPAT:	2003/09/15
_	3	(implant or implantation or implantated or	US-PGPUB;	15:01
		, · · · · · · · · · · · · · · · · · · ·	1	15:01
		implantating)) and (single adj crystal) and laser	EPO; JPO; DERWENT;	
		laser		
		(abligue poerdo (ion or etern) poerdo	IBM_TDB	2003/09/15
•	8	(oblique near10 (ion or atom) near10	USPAT;	1
		(implant or implantation or implantated or	US-PGPUB;	15:01
		implantating)) and (single adj crystal) and laser and mask	EPO; JPO;	
		laser and mask	DERWENT;	
	2	(abligue vacuato (iau au atams) vacuato	IBM_TDB	2002/00/45
-	_	(oblique near10 (ion or atom) near10	USPAT; US-PGPUB:	2003/09/15
		(implant or implantation or implantated or		15:02
		implantating)) and (single adj crystal) and	EPO; JPO;	
		laser and mask and (parasitic near	DERWENT;	
	40450	resistance)	IBM_TDB	2003/09/15
-	10159	((atom or ion) near (implant or implanting or	USPAT;	2003/09/15 15:03
	İ	implanted or implantation)).clm.	US-PGPUB;	19:03
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	o	((atom or ion) near (implant or implanting or	USPAT;	2003/09/15
_		implanted or implantation)).clm. and	US-PGPUB;	15:04
		oblique.clm. and (parasitic near resistance)	EPO; JPO;	13.04
		and (amorphous or amorphize or	DERWENT;	
		and (amorphous or amorphize or amorphizing or amorphized).clm.	IBM_TDB	
-	12	((atom or ion) near (implant or implanting or	USPAT;	2003/09/15
	.2	implanted or implantation)).clm. and	US-PGPUB;	15:04
		oblique.clm. and (amorphous or amorphize	EPO; JPO;	
		or amorphizing or amorphized).clm.	DERWENT;	
	1		IBM_TDB	
_	4	((atom or ion) near (implant or implanting or	USPAT;	2003/09/15
]	implanted or implantation)).clm. and	US-PGPUB;	15:06
		oblique.clm. and (amorphous or amorphize	EPO; JPO;	
		or amorphizing or amorphized).clm. and	DERWENT;	
		(single adj crystal)	IBM_TDB	
-	2	gate and source and drain and (single adj	USPAT;	2003/09/15
	_	crystal) and (insulating or dielectric) and	US-PGPUB;	15:08
	}	(atom or ion) and (amorphize or	EPO; JPO;	
		am rphizing or amorphiz d) and oblique	DERWENT;	
	1		IBM_TDB	
		 	.Bm_1DB	<u> </u>

•	1	gate and s urce and drain and (ingl adj	USPAT;	2003/09/15
		crystal) and (insulating or diel ctri) and	US-PGPUB;	15:08
		(atom or ion) and (am rphize r	EPO; JPO;	
		amorphizing ram rphized) and obliqu and	DERWENT;	
ı		las r	IBM_TDB	
-	70	gate and source and drain and (single adj	USPAT;	2003/09/15
		crystal) and (insulating or dielectric) and	US-PGPUB;	15:09
		(atom or ion) and (amorphous or amorphize	EPO; JPO;	
		or amorphizing or amorphized) and oblique	DERWENT:	
		and laser and (irradiate or irradiating or	IBM_TDB	
		irradiated or irradiation or anneal or	_	
		annealing or annealed) and mask		
-	9	gate and source and drain and (single adj	USPAT;	2003/09/15
İ		crystal) and (insulating or dielectric) and	US-PGPUB;	15:11
İ		(atom or ion) and (amorphous or amorphize	EPO; JPO;	
		or amorphizing or amorphized) and oblique	DERWENT;	
		and laser and (irradiate or irradiating or	IBM_TDB	
		irradiated or irradiation or anneal or	-	
		annealing or annealed) and mask and		
		(sidewall or (side near wall)) and junction		
		and (impurity or impurities)		
-	2	gate and source and drain and (single adj	USPAT;	2003/09/15
	_	crystal) and (insulating or dielectric) and	US-PGPUB;	15:16
		(atom or ion) and (amorphous or amorphize	EPO; JPO;	
		or amorphizing or amorphized) and oblique	DERWENT;	
		and laser and (irradiate or irradiating or	IBM TDB	
		irradiated or irradiation or anneal or	_	
		annealing or annealed) and mask and		
		(sidewall or (side near wall)) and junction		
		and (impurity or impurities) and (shallow		
		and deep)		
_	1	gate and source and drain and (single adj	USPAT;	2003/09/15
		crystal) and (shallow near junction) and	US-PGPUB;	15:17
		(deep junction) and impurity and (atom or	EPO; JPO;	
		ion) and (amorphizing or amorphized or	DERWENT;	
ľ	}	amorphize) and (seeping or seep or seeped)	IBM_TDB	
	1	gate and source and drain and (single ad)	USPAT;	2003/09/15
i		crystal) and (shallow near junction) and	US-PGPUB;	15:17
		(deep junction) and impurity and (atom or	EPO; JPO;	
		ion) and (amorphizing or amorphized or	DERWENT;	
		amorphize) and (seeping or seep or seeped)	IBM_TDB	
İ		and capacitance		
_	1	gate and source and drain and (single adj	USPAT;	2003/09/15
		crystal) and (shallow near junction) and	US-PGPUB;	15:18
		(deep junction) and impurity and (atom or	EPO; JPO;	
į	ļ	ion) and (amorphous or amorphizing or	DERWENT;	
		amorphized or amorphize) and (seeping or	IBM_TDB	

-	1	gate and s urce and drain and (single adj	USPAT;	2003/09/15
	1	crystal) and (shall w n ar junction) and	US-PGPUB:	15:18
		(de p jun ti n) and (impurity or atom or	EPO; JPO;	
	1	ion) and (amorphous or am rphizing r	DERWENT;	
		amorphized or amorphize) and (seeping or	IBM TDB	
		seep or seeped) and capacitance		
_	1	(shallow near junction) and (deep junction)	USPAT;	2003/09/15
	•	and (impurity or atom or ion) and	US-PGPUB;	15:18
		(amorphous or amorphizing or amorphized	EPO; JPO;	10110
		or amorphize) and (seeping or seep or	DERWENT:	
		seeped) and capacitance	IBM_TDB	
_	1	(shallow near junction) and (deep junction)	USPAT;	2003/09/15
_	•	and (impurity or atom or ion) and	US-PGPUB;	15:18
		(amorphous or amorphizing or amorphized	EPO; JPO;	13.10
		or amorphize) and (seeping or seep or	DERWENT;	
			IBM TDB	
	1	seeped)	USPAT;	2003/09/15
-	1	(shallow near junction) and (deep near junction) and (impurity or atom or ion) and	US-PGPUB;	15:19
		, , , , , , , , , , , , , , , , , , , ,	1	13:19
	ļ	(amorphous or amorphizing or amorphized	EPO; JPO; DERWENT;	
		or amorphize) and (seeping or seep or	IBM TDB	
	55	seeped)	_	2003/09/15
-	55	(US-5569954-\$ or US-5824574-\$ or	USPAT;	
		US-6001461-\$ or US-5709958-\$ or	US-PGPUB;	15:19
		US-6534373-\$ or US-6391695-\$ or	JPO	
		US-4597804-\$ or US-5955759-\$ or		
		US-6458200-\$ or US-5698869-\$ or		
		US-5291274-\$ or US-5229319-\$ or		
		US-5908307-\$ or US-5736438-\$ or	}	
		US-5514880-\$ or US-5693959-\$ or		
		US-6610569-\$ or US-6524924-\$ or		
		US-6455875-\$ or US-6315384-\$ or		
		US-6267471-\$ or US-6180957-\$ or		
		US-6133094-\$ or US-5962897-\$ or		
		US-5930638-\$ or US-5793097-\$).did. or		
		(US-6437367-\$ or US-6436815-\$ or	Ì	
		US-5963278-\$ or US-5933205-\$ or		
		US-5856228-\$ or US-5643806-\$ or		
		US-5568288-\$ or US-5541124-\$ or		
		US-5287205-\$ or US-6255146-\$ or	İ	
	İ	US-6245622-\$ or US-6188085-\$ or		
		US-6017781-\$ or US-5612230-\$ or		
		US-5600154-\$ or US-5428237-\$ or		
		US-5270227-\$ or US-5164806-\$ or		
		US-6184088-\$).did. or (US-20020121654-\$ or		
		US-20020073918-\$ or		
		US-20020011627-\$).did. or		
		(JP-2002280548-\$ or JP-2002329864-\$ or		
		JP-63009152-\$ or JP-11087361-\$ or	İ	
	1	JP-09309713-\$ or JP-06267974-\$ r		
	L	JP-05047794-\$).did.	<u></u>	<u> </u>

	1	//US FECODE 4 & US FOO 4574 &	HODAT	0000/00/45
-	1	((US-5569954-\$ r US-5824574-\$ or	USPAT;	2003/09/15
		U -6001461-\$ r US-5709958-\$ r	US-PGPUB;	15:19
		US-6534373-\$ r US-6391695-\$ or	EPO; JPO;	
		US-4597804-\$ r US-5955759-\$ or	DERWENT;	
		US-6458200-\$ r US-5698869-\$ r	IBM_TDB	
ĺ		US-5291274-\$ or US-5229319-\$ or	!	
		US-5908307-\$ or US-5736438-\$ or		
		US-5514880-\$ or US-5693959-\$ or		
		US-6610569-\$ or US-6524924-\$ or		
		US-6455875-\$ or US-6315384-\$ or		
		US-6267471-\$ or US-6180957-\$ or		
		US-6133094-\$ or US-5962897-\$ or		
		US-5930638-\$ or US-5793097-\$).did. or		
		(US-6437367-\$ or US-6436815-\$ or		
		US-5963278-\$ or US-5933205-\$ or		
		US-5856228-\$ or US-5643806-\$ or		
		US-5568288-\$ or US-5541124-\$ or		
		US-5287205-\$ or US-6255146-\$ or		
		US-6245622-\$ or US-6188085-\$ or		
		US-6017781-\$ or US-5612230-\$ or		
		US-5600154-\$ or US-5428237-\$ or		
		US-5270227-\$ or US-5164806-\$ or		
		US-6184088-\$).did. or (US-20020121654-\$ or		
		US-20020073918-\$ or	:	
		• • • • • • • • • • • • • • • • • • • •		
		US-20020011627-\$).did. or		
		(JP-2002280548-\$ or JP-2002329864-\$ or		
		JP-63009152-\$ or JP-11087361-\$ or		
		JP-09309713-\$ or JP-06267974-\$ or		
		JP-05047794-\$).did.) and seeping		
'	271	seeping.clm.	USPAT;	2003/09/15
			US-PGPUB;	15:19
İ			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	seeping.clm. and junction.clm.	USPAT;	2003/09/15
			US-PGPUB;	15:21
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(source and drain and gate and (single adj	USPAT;	2003/09/15
	i	crystal) and (atom or impurity or ion) and	US-PGPUB;	15:22
		(shallow adj junction) and (deep adj	EPO; JPO;	
		junction) and capacitance).clm.	DERWENT;	
		•	IBM_TDB	
-	1	((single adj crystal) and (atom or impurity	USPAT;	2003/09/15
	-	or ion) and (shallow adj junction) and (deep	US-PGPUB;	15:22
		adj junction) and capacitance).clm.	EPO; JPO;	
		and the second s	DERWENT;	
			IBM_TDB	
			IOM_IUD	

-	22	((shallow adj juncti n) and (d ep adj	USPAT;	2003/09/15
		junction)).clm.	US-PGPUB;	15:23
		•	EPO; JPO;	
			DERWENT:	
			IBM TDB	
-	5	(((shallow adj junction) and (deep adj	USPAT;	2003/09/15
		junction)).clm.) and ((ion or atom or	US-PGPUB;	15:24
		impurity) near (implant or implanting or	EPO; JPO;	
		implanted or implantation)).clm.	DERWENT;	
			IBM_TDB	
-	2	((shallow adj junction) and (deep adj	USPAT;	2003/09/15
		junction)).clm. and ((ion or atom or	US-PGPUB;	15:25
	[impurity) near (implant or implanting or	EPO; JPO;	
		implanted or implantation)).clm. and	DERWENT;	
		(amorphous or amorphize or amorphizing or	IBM_TDB	
		amorphized).clm.	_	
-	3	((shallow near junction) and (deep near	USPAT;	2003/09/15
		junction)).clm. and ((ion or atom or	US-PGPUB;	15:26
		impurity) near (implant or implanting or	EPO; JPO;	
		implanted or implantation)).clm. and	DERWENT;	
		(amorphous or amorphize or amorphizing or	IBM_TDB	
		amorphized).clm.	_	
-	0	(((shallow near junction) and (deep near	USPAT;	2003/09/15
		junction)).clm. and ((ion or atom or	US-PGPUB;	15:25
		impurity) near (implant or implanting or	EPO; JPO;	
		implanted or implantation)).clm. and	DERWENT;	
		(amorphous or amorphize or amorphizing or	IBM_TDB	
	i	amorphized).clm.) and oblique		
-	1	((shallow near junction) and (deep near	USPAT;	2003/09/15
		junction)) and ((ion or atom or impurity)	US-PGPUB;	15:27
		near (implant or implanting or implanted or	EPO; JPO;	
]	implantation)) and (amorphous or	DERWENT;	
		amorphize or amorphizing or amorphized)	IBM_TDB	
		and laser and (single adj crystal) and	ļ	
		oblique		
-	9	((shallow near junction) and (deep near	USPAT;	2003/09/15
		junction)) and ((ion or atom or impurity)	US-PGPUB;	15:28
		near (implant or implanting or implanted or	EPO; JPO;	
		implantation)) and (amorphous or	DERWENT;	
		amorphize or amorphizing or amorphized)	IBM_TDB	
]	and laser and (single adj crystal)		
•	4	(laser adj (irradiate or irradiatig or	USPAT;	2003/09/15
		irradiated or irradiation or anneal or	US-PGPUB;	15:30
		annealing or annealed)) and oblique and	EPO; JPO;	
		((atom or impurity or ion) near (implant or	DERWENT;	
		implanting or implanted or implantation))	IBM_TDB	
		and (amorphize or amorphizing or		
		amorphized)		

•	4	(laser adj (irradiate r irradiatig r	USPAT;	2003/09/15
		irradiated or irradiati n or anneal or	US-PGPUB;	15:30
		annealing or anneal d)) and blique and	EPO; JPO;	
		((atom rimpurity ri n) near(implant r	DERWENT;	
		implanting or implant d or implantation))	IBM_TDB	
		and (amotphous or amorphize or		
		amorphizing or amorphized)		
-	101	(laser adj (irradiate or irradiatig or	USPAT;	2003/09/15
		irradiated or irradiation or anneal or	US-PGPUB;	15:30
		annealing or annealed)) and oblique and	EPO: JPO:	10.00
		((atom or impurity or ion) near (implant or	DERWENT;	
		implanting or implanted or implantation))	IBM_TDB	
		and (amorphous or amorphize or	10111_100	
		· · · · · · · · · · · · · · · · · · ·		
	4	amorphizing or amorphized)	HEDAT.	2002/00/45
•	4	(laser adj (irradiate or irradiatig or	USPAT;	2003/09/15
		irradiated or irradiation or anneal or	US-PGPUB;	15:31
		annealing or annealed)) and oblique and	EPO; JPO;	
		((atom or impurity or ion) near (implant or	DERWENT;	
		implanting or implanted or implantation))	IBM_TDB	
	1	and (amorphous or amorphize or		
		amorphizing or amorphized) and (single adj		
		crystal) and ((deep or shallow) near		
		junction)		
-	4	(laser adj (irradiate or irradiatig or	USPAT;	2003/09/15
	1	irradiated or irradiation or anneal or	US-PGPUB;	15:32
	1	annealing or annealed)) and oblique and	EPO; JPO;	
		((atom or impurity or ion) near (implant or	DERWENT;	
	}	implanting or implanted or implantation))	IBM_TDB	
		and (amorphous or amorphize or		
		amorphizing or amorphized) and (single adj		
		crystal) and ((deep or shallow) near		
		junction) and oblique		
-	4	(laser adj (irradiate or irradiating or	USPAT;	2003/09/15
		irradiated or irradiation or anneal or	US-PGPUB;	15:32
		annealing or annealed)) and oblique and	EPO; JPO;	
]	((atom or impurity or ion) near (implant or	DERWENT;	
	1 1	implanting or implanted or implantation))	IBM_TDB	
		and (amorphous or amorphize or	10M_100	
	1	•		
	Į l	amorphizing or amorphized) and (single adj		
]	crystal) and ((deep or shallow) near		
	_	junction) and oblique		
•	5	(laser near (irradiate or irradiating or	USPAT;	2003/09/15
		irradiated or irradiation or anneal or	US-PGPUB;	15:33
		annealing or annealed)) and oblique and	EPO; JPO;	
		((atom or impurity or ion) near (implant or	DERWENT;	
		implanting or implanted or implantation))	IBM_TDB	
		and (amorphous or amorphize or		
	[amorphizing or amorphized) and (single		
		bear crystal) and ((deep or shallow) near		
		juncti n)		

-	4	(laser n ar (irradiat or irradiating or	USPAT;	2003/09/15
		irradiat d r irradiation or ann al r	US-P PUB;	15:35
		annealing rannealed)) and oblique and	EPO; JPO;	
		((atom rimpurity ri n) near(implant r	DERWENT;	
	1	implanting or implanted or implantation))	IBM_TDB	
		and (amorphous or amorphize or		
		amorphizing or amorphized) and (single		
		near crystal) and ((deep or shallow) near		
	-	junction)		